
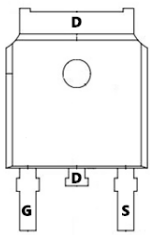


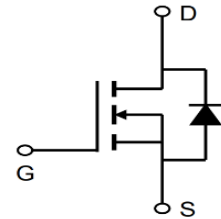
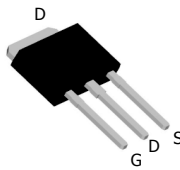
TMN3050Y

N-Channel Enhancement Mosfet

<p>General Description</p> <ul style="list-style-type: none"> • Low $R_{DS(ON)}$ • RoHS and Halogen-Free Compliant <p>Applications</p> <ul style="list-style-type: none"> • Load switch • PWM 	<p>General Features</p> <p>$V_{DS} = 30V$ $I_D = 50A$</p> <p>$R_{DS(ON)} = 7.6 m\Omega$ (typ.) @ $V_{GS} = 10V$</p> <p>100% UIS Tested 100% R_g Tested</p> 
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Y:TO-251S-3L



Marking: 50N03

Absolute Maximum Ratings				
Symbol	Parameter	Rating		Units
		10s	Steady State	
V_{DS}	Drain-Source Voltage	30		V
V_{GS}	Gate-Source Voltage	± 20		V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	50		A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	26		A
I_{DM}	Pulsed Drain Current ²	168		A
EAS	Single Pulse Avalanche Energy ³	33		mJ
I_{AS}	Avalanche Current	23.8		A
$P_D @ T_C = 25^\circ C$	Total Power Dissipation ⁴	30.5		W
T_{STG}	Storage Temperature Range	-55 to 175		$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 175		$^\circ C$

Thermal Data				
Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	5.26	$^\circ C/W$



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Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=30V, V_{GS}=0V,$	-	-	1.0	μA
I_{GSS}	Gate to Body Leakage Current	$V_{DS}=0V, V_{GS}=\pm 20V$	-	-	± 100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.5	2.5	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note3	$V_{GS}=10V, I_D=20A$	-	7.6	10	m Ω
		$V_{GS}=4.5V, I_D=10A$	-	10.2	17	
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS}=15V, V_{GS}=0V,$ $f=1.0MHz$	-	1011	-	pF
C_{oss}	Output Capacitance		-	142	-	pF
C_{rss}	Reverse Transfer Capacitance		-	119	-	pF
Q_g	Total Gate Charge	$V_{DS}=15V, I_D=20A,$ $V_{GS}=10V$	-	19	-	nC
Q_{gs}	Gate-Source Charge		-	6.3	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	4.5	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=30V,$ $I_D=2A, R_{GEN}=3\Omega,$ $V_{GS}=10V$	-	6	-	ns
t_r	Turn-on Rise Time		-	5	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	25	-	ns
t_f	Turn-off Fall Time		-	7	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	50	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	160	A
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS}=0V, I_S=30A$	-	-	1.2	V
t_{rr}	Body Diode Reverse Recovery Time	$I_F=30A, di/dt=100A/\mu s$	-	7	-	ns
Q_{rr}	Body Diode Reverse Recovery Charge		-	6.3	-	nC

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition: $T_J=25^\circ\text{C}$, $V_{DD}=15V$, $V_G=10V$, $R_G=25\Omega$, $L=0.5mH$, $I_{AS}=11.5A$

3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$

Typical Performance Characteristics

Figure 1: Output Characteristics

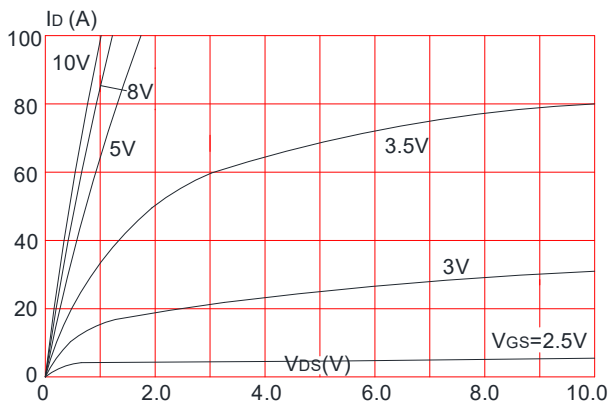


Figure 2: Typical Transfer Characteristics

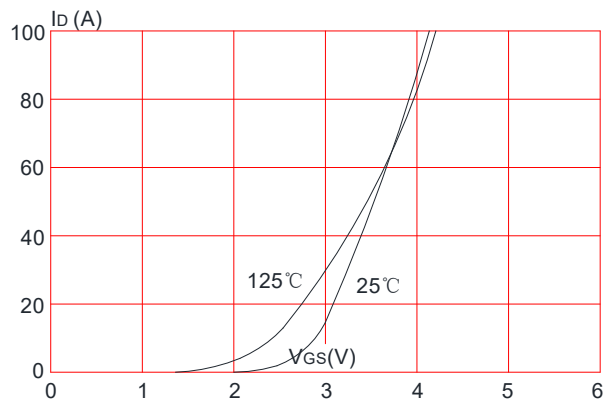


Figure 3: On-resistance vs. Drain Current

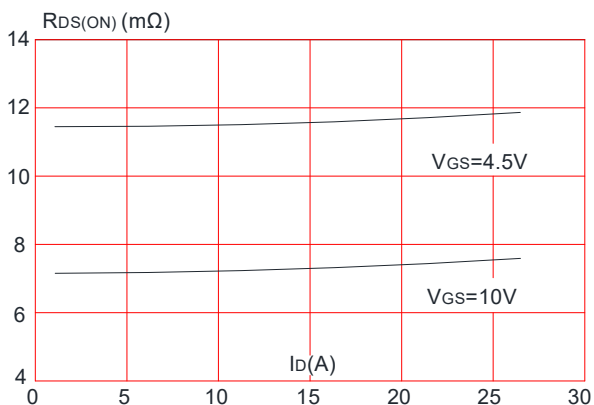


Figure 4: Body Diode Characteristics

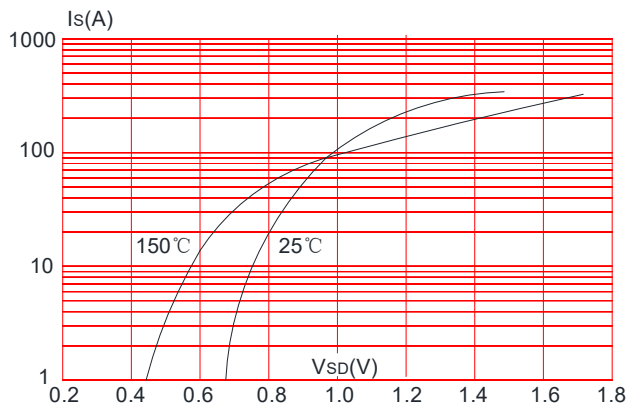


Figure 5: Gate Charge Characteristics

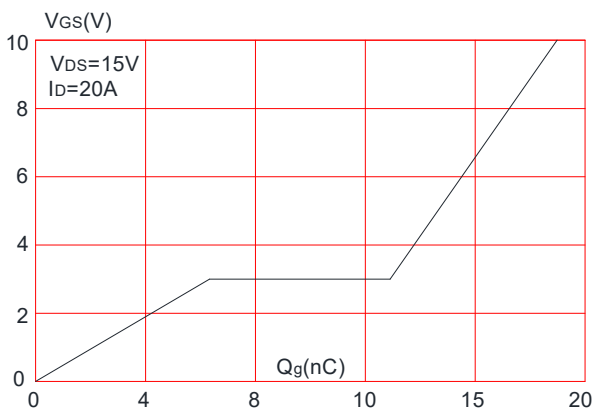
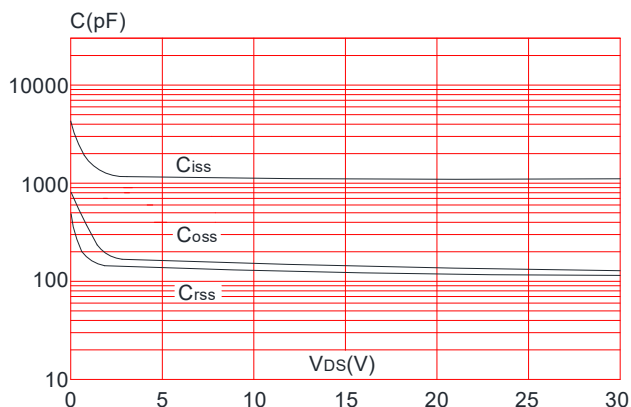


Figure 6: Capacitance Characteristics



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Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

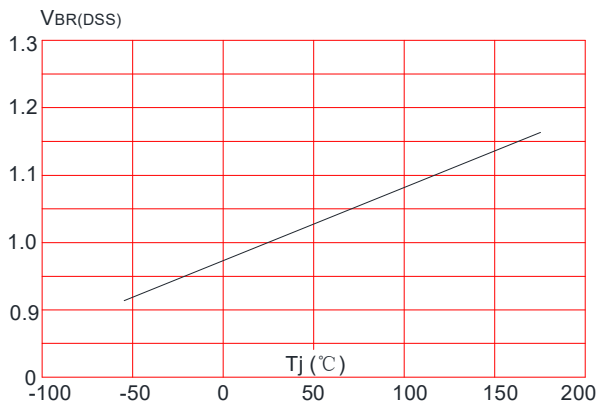


Figure 8: Normalized on Resistance vs. Junction Temperature

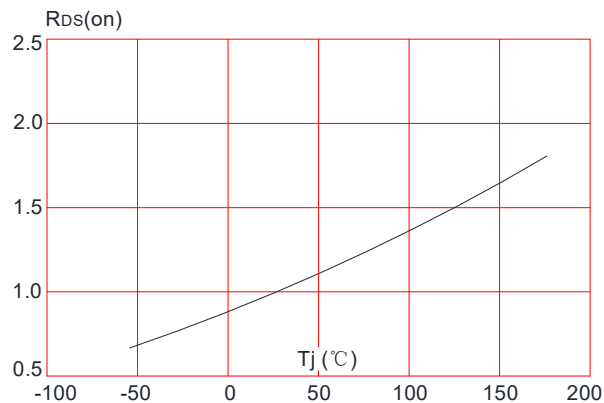


Figure 9: Maximum Safe Operating Area

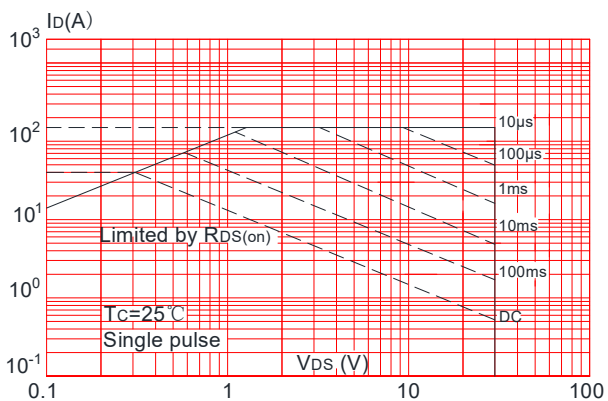
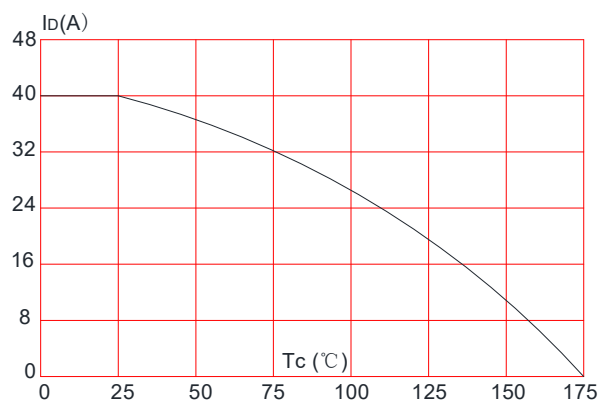
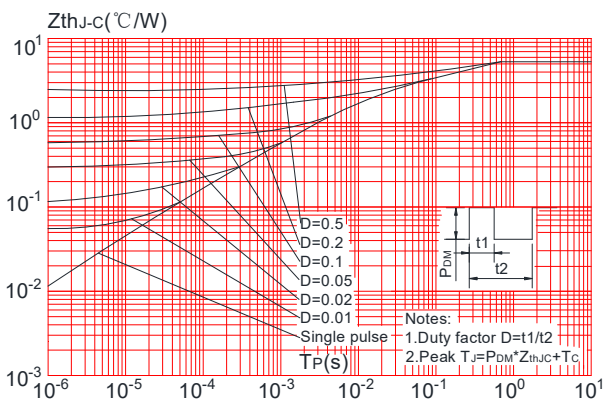


Figure 10: Maximum Continuous Drain Current vs. Case Temperature



Maximum Effective Transient Thermal Impedance, Junction-to-Case



Test Circuit

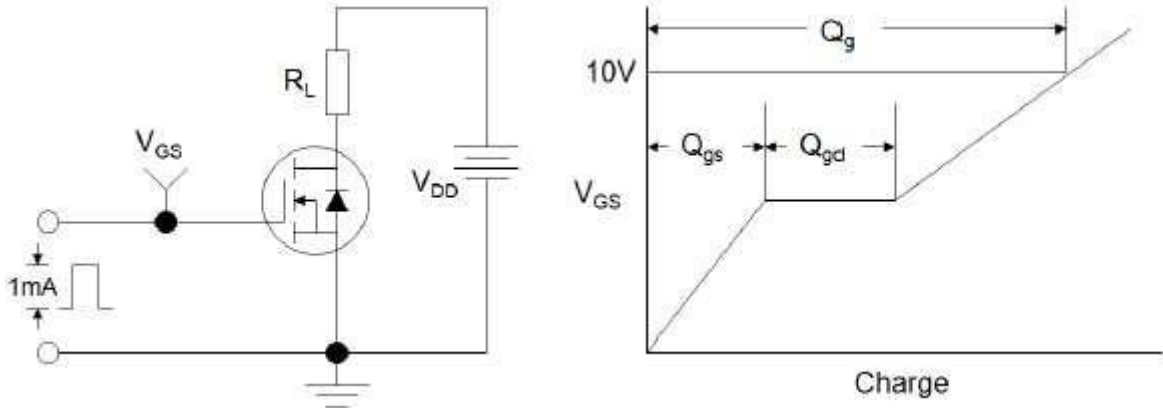


Figure1:Gate Charge Test Circuit & Waveform

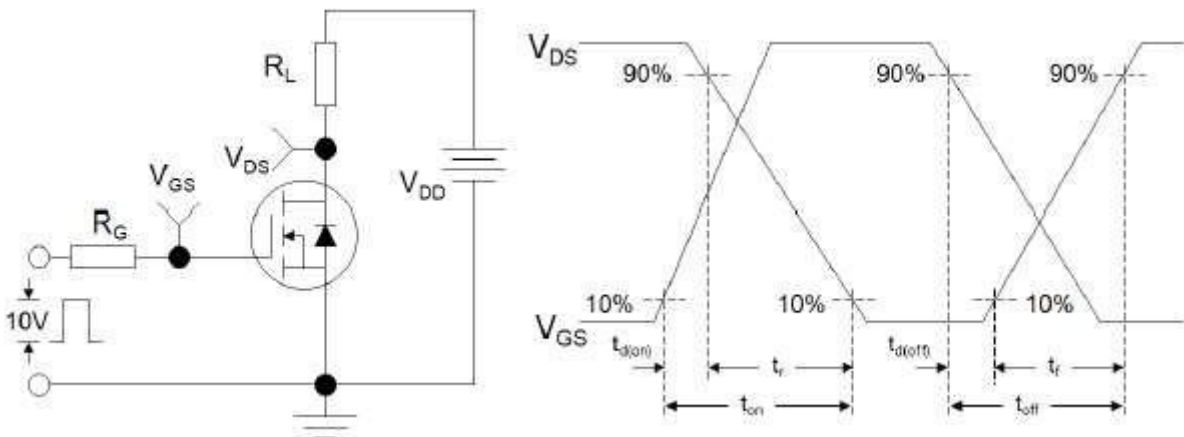


Figure 2: Resistive Switching Test Circuit & Waveforms

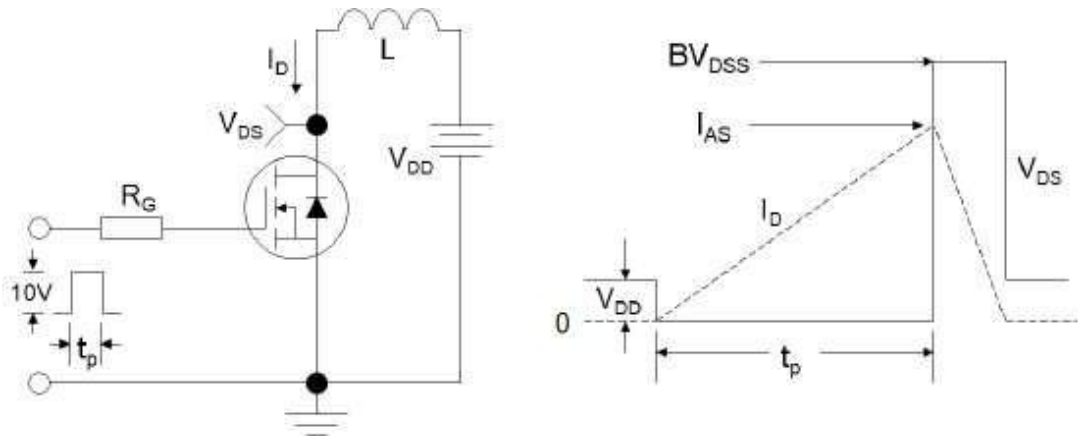
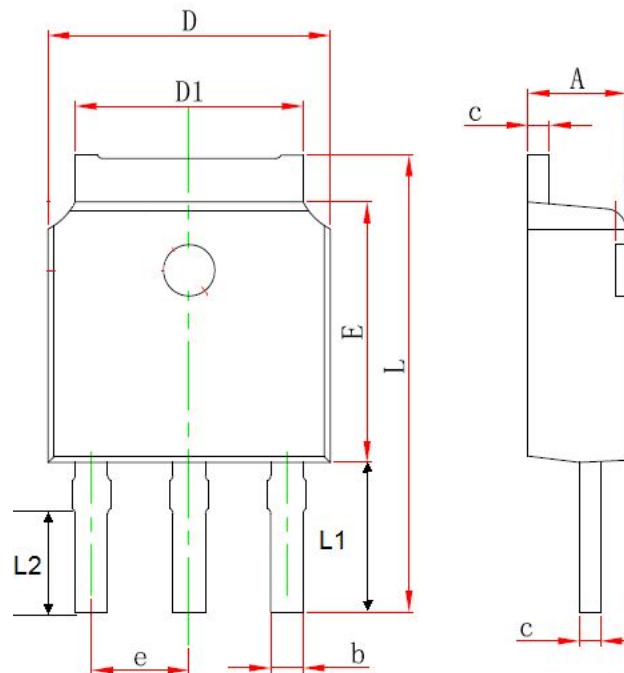


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms

Package Information: TO-251S-3L

UNIT: mm

SYMBOL	min	nom	max
A	2.20		2.40
b	0.50		0.85
C	0.45	0.50	0.60
D	6.50		6.70
D1	5.10		5.50
E	5.9		6.20
e	2.18	2.29	2.38
L	11.00		12.40
L1	4.8		5.3
L2	3.5		4.2



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